# 2-Bit 100 Mb/s Configurable **Dual-Supply Level Translator**

The NLSX3012 is a 2-bit configurable dual-supply bidirectional level translator without a direction control pin. The I/O  $V_{CC}$ - and I/O V<sub>L</sub>-ports are designed to track two different power supply rails, V<sub>CC</sub> and V<sub>L</sub> respectively. The V<sub>CC</sub> supply rail is configurable from 1.3 V to 4.5 V while the V<sub>L</sub> supply rail is configurable from 0.9 V to (V<sub>CC</sub> -0.4) V. This allows lower voltage logic signals on the  $V_L$  side to be translated into higher voltage logic signals on the V<sub>CC</sub> side, and vice-versa. Both I/O ports are auto-sensing; thus, no direction pin is required.

The Output Enable (EN) input, when Low, disables both I/O ports by putting them in 3-state. This significantly reduces the supply currents from both V<sub>CC</sub> and V<sub>L</sub>. The EN signal is designed to track  $V_L$ .

#### **Features**

- Wide High-Side V<sub>CC</sub> Operating Range: 1.3 V to 4.5 V Wide Low-Side V<sub>L</sub> Operating Range: 0.9 V to (V<sub>CC</sub> - 0.4) V
- High-Speed with 140 Mb/s Guaranteed Date Rate for V<sub>L</sub> >
- Low Bit-to-Bit Skew
- Overvoltage Tolerant Enable and I/O Pins
- Non-preferential Powerup Sequencing
- Small packaging: UDFN8, SO-8, Micro8
- These are Pb-Free Devices

#### **Typical Applications**

- Typical ApplicationsMobile Phones, PDAs, Other Portable Devices
- THIS DEVI • PC and Laptops



## ON Semiconductor®

http://onsemi.com

#### **MARKING DIAGRAMS**



**UDFN8 MU SUFFIX** CASE 517AJ



Specific Device Code = Date Code

Pb-Free Package



SO<sub>-8</sub> D'SUFFIX



Assembly Location

Wafer Lot = Year

= Work Week

= Pb-Free Package



Micro8 **DM SUFFIX** CASE 846A



= Assembly Location

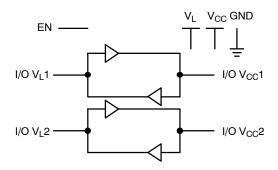
= Year = Work Week W = Pb-Free Package

# **ORDERING INFORMATION**

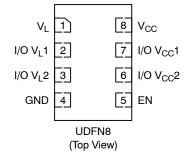
Device	Package	Shipping <sup>†</sup>
NLSX3012MUTAG	UDFN8 (Pb-Free)	3000/Tape & Reel
NLSX3012DR2G	SO-8 (Pb-Free)	2500/Tape & Reel
NLSX3012DMR2G	Micro8 (Pb-Free)	4000/Tape & Reel

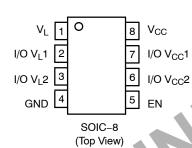
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

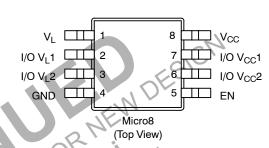
# **LOGIC DIAGRAM**



#### **PIN ASSIGNMENTS**







# **PIN ASSIGNMENT**

Pins	Description
V <sub>CC</sub>	V <sub>CC</sub> Input Voltage
V <sub>L</sub>	V <sub>L</sub> Input Voltage
GND	Ground
EN	Output Enable
I/O V <sub>CC</sub> n	I/O Port, Referenced to V <sub>CC</sub>
I/O V <sub>L</sub> n	I/O Port, Referenced to V <sub>L</sub>
THI	SDEVICEPLERESEN

# FUNCTION TABLE

EN	Operating Mode	
16.100	Hi-Z	
Н //	I/O Buses Connected	

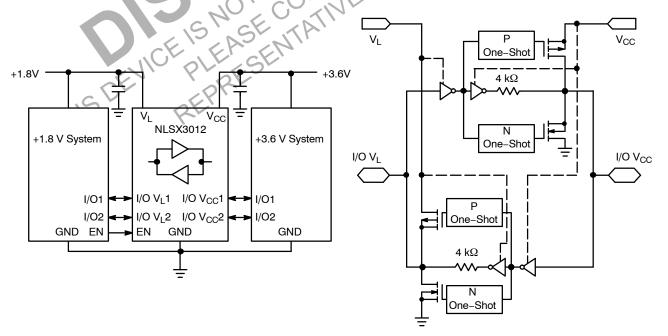
#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Condition	Unit
V <sub>CC</sub>	V <sub>CC</sub> Supply Voltage	-0.5 to +5.5		V
VL	V <sub>L</sub> Supply Voltage	-0.5 to +5.5		V
I/O V <sub>CC</sub>	V <sub>CC</sub> -Referenced DC Input/Output Voltage	-0.5 to (V <sub>CC</sub> + 0.3)		V
I/O V <sub>L</sub>	V <sub>L</sub> -Referenced DC Input/Output Voltage	-0.5 to (V <sub>L</sub> + 0.3)		V
V <sub>EN</sub>	Enable Control Pin DC Input Voltage	-0.5 to +5.5		V
I <sub>IK</sub>	Input Diode Clamp Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	Output Diode Clamp Current	-50	V <sub>O</sub> < GND	mA
I <sub>CC</sub>	DC Supply Current Through V <sub>CC</sub>	±100		mA
IL	DC Supply Current Through V <sub>L</sub>	±100		mA
I <sub>GND</sub>	DC Ground Current Through Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature	-65 to +150	N- N	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	V <sub>CC</sub> Supply Voltage	1.3	4.5	V
V <sub>L</sub>	V <sub>L</sub> Supply Voltage	0.9	V <sub>CC</sub> - 0.4	V
V <sub>EN</sub>	Enable Control Pin Voltage	GND	4.5	V
V <sub>IO</sub>	Bus Input/Output Voltage	GND	4.5 4.5	V
T <sub>A</sub>	Operating Temperature Range	-40	+85	°C
ΔΙ/ΔV	Input Transition Rise or Rate V <sub>I</sub> , V <sub>IO</sub> from 30% to 70% of V <sub>CC</sub> ; V <sub>CC</sub> = 3.3 V $\pm$ 0.3 V	0	10	ns



**Figure 1. Typical Application Circuit** 

Figure 2. Simplified Functional Diagram (1 I/O Line) (EN = 1)

#### DC ELECTRICAL CHARACTERISTICS

					-4	0°C to +85	s°C	
Symbol	Parameter	Test Conditions (Note 1)	V <sub>CC</sub> (V) (Note 2)	<b>V<sub>L</sub> (V)</b> (Note 3)	Min	Typ (Note 4)	Max	Unit
V <sub>IHC</sub>	I/O V <sub>CC</sub> Input HIGH Voltage		1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	0.8 * V <sub>CC</sub>	-	=	٧
V <sub>ILC</sub>	I/O V <sub>CC</sub> Input LOW Voltage		1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	-	-	0.2 * V <sub>CC</sub>	٧
V <sub>IHL</sub>	I/O V <sub>L</sub> Input HIGH Voltage		1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	0.8 * V <sub>L</sub>	-	_	٧
V <sub>ILL</sub>	I/O V <sub>L</sub> Input LOW Voltage		1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	-	-	0.2 * V <sub>L</sub>	٧
$V_{IH}$	Control Pin Input HIGH Voltage	T <sub>A</sub> = +25°C	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	0.8 * V <sub>L</sub>	-	-	٧
V <sub>IL</sub>	Control Pin Input LOW Voltage	T <sub>A</sub> = +25°C	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		-	0.2 * V <sub>L</sub>	٧
V <sub>OHC</sub>	I/O V <sub>CC</sub> Output HIGH Voltage	I/O V <sub>CC</sub> Source Current = 20 μA	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	0.8 * V <sub>CC</sub>	OFS	_	٧
V <sub>OLC</sub>	I/O V <sub>CC</sub> Output LOW Voltage	I/O V <sub>CC</sub> Sink Current = 20 μA	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	EN	_	0.2 * V <sub>CC</sub>	٧
V <sub>OHL</sub>	I/O V <sub>L</sub> Output HIGH Voltage	I/O V <sub>L</sub> Source Current = 20 μA	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	0.8 * V <sub>L</sub>	-	-	٧
V <sub>OLL</sub>	I/O V <sub>L</sub> Output LOW Voltage	I/O V <sub>L</sub> Sink Current = 20 μA	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	71	D/-	0.2 * V <sub>L</sub>	V

- Normal test conditions are V<sub>EN</sub> = 0 V, C<sub>IOVCC</sub> = 15 pF and C<sub>IOVL</sub> = 15 pF, unless otherwise specified.
   V<sub>CC</sub> is the supply voltage associated with the high voltage port, and V<sub>CC</sub> ranges from +1.3 V to 4.5 V under normal operating conditions.
   V<sub>L</sub> is the supply voltage associated with the low voltage port. V<sub>L</sub> must be less than or equal to (V<sub>CC</sub> 0.4) V during normal operation. However, during startup and shutdown conditions, V<sub>L</sub> can be greater than (V<sub>CC</sub> 0.4) V.
   Typical values are for V<sub>CC</sub> = +2.8 V, V<sub>L</sub> = +1.8 V and T<sub>A</sub> = +25°C. All units are production tested at T<sub>A</sub> = +25°C. Limits over the operating temperature range are guaranteed by design. HIS DEVICE PLEASENTATIVE PREPRESENTATIVE PREPRESENTATIVE
- temperature range are guaranteed by design.

#### **POWER CONSUMPTION**

		Test Conditions	V <sub>CC</sub> (V)	V <sub>L</sub> (V)	-40	°C to +85	5°C	
Symbol	Parameter	(Note 5)	(Note 6)	(Note 7)	Min	Тур	Max	Unit
I <sub>Q-VCC</sub>	Supply Current from V <sub>CC</sub>	$\begin{split} EN &= V_{L;} \text{ I/O } V_{CCn} = 0 \text{ V, I/O } V_{Ln} = 0 \text{ V,} \\ \text{I/O } V_{CCn} &= V_{CC} \text{ or I/O } V_{Ln} = V_{L} \text{ and } I_{o} = 0 \end{split}$	1.3 to 3.6	0.9 to (V <sub>CC</sub> – 0.4)	-	-	1.0	μΑ
$I_{Q-VL}$	Supply Current from V <sub>L</sub>	$ \begin{split} &EN = V_{L;} \text{ I/O } V_{CCn} = 0 \text{ V, I/O } V_{Ln} = 0 \text{ V,} \\ &I/O  V_{CCn} = V_{CC} \text{ or I/O } V_{Ln} = V_{L} \text{ and } I_{o} = 0 \end{split} $	1.3 to 3.6	0.9 to (V <sub>CC</sub> – 0.4)	-	-	1.0	μΑ
		$ \begin{split} & EN = V_L, \ I/O \ V_{CCn} = 0 \ V, \ I/O \ V_{Ln} = 0 \ V, \\ & I/O \ V_{CCn} = V_{CC} \ or \ I/O \ V_{Ln} = (V_{CC} - \\ & 0.2 \ V) \ and \ I_0 = 0 \end{split} $		< (V <sub>CC</sub> – 0.2)	-	-	2.0	
I <sub>TS-VCC</sub>	V <sub>CC</sub> Tristate Output Mode Supply Current	EN = 0 V	1.3 to 3.6	0.9 to (V <sub>CC</sub> – 0.4)	-	-	1.0	μΑ
I <sub>TS-VL</sub>	V <sub>L</sub> Tristate Output	EN = 0 V	1.3 to 3.6	0.9 to (V <sub>CC</sub> – 0.4)	_	-	0.2	μΑ
	Mode Supply Current	EN = 0 V		V <sub>CC</sub> – 0.2	1	-	2.0	
I <sub>OZ</sub>	I/O Tristate Output	EN = 0 V	1.3 to 3.6	0.9 to (V <sub>CC</sub> – 0.4)		- \	0.15	μΑ
	Mode Leakage Current	EN = 0 V		V <sub>CC</sub> - 0.2		(5)	2.0	
I <sub>EN</sub>	Output Enable Pin Input Current	-	1.3 to 3.6	0.9 to (V <sub>CC</sub> – 0.4)	N	) <u>-</u>	1.0	μΑ

- Normal test conditions are V<sub>EN</sub> = 0 V, C<sub>IOVCC</sub> = 15 pF and C<sub>IOVL</sub> = 15 pF, unless otherwise specified.
   V<sub>CC</sub> is the supply voltage associated with the logh voltage port, and V<sub>CC</sub> ranges from +1.3 V to 4.5 V under normal operating conditions.
   V<sub>L</sub> is the supply voltage associated with the low voltage port. V<sub>L</sub> must be less than or equal to (V<sub>CC</sub> 0.4) V during normal operation. However,
- 6. V<sub>CC</sub> is the supply voltage associated with the high voltage port, and V<sub>CC</sub> ranges from +1.3 V to 4.5 V under normal operating conditions.
  7. V<sub>L</sub> is the supply voltage associated with the low voltage port. V<sub>L</sub> must be less than or equal to (V<sub>CC</sub> 0.4) V during normal operation. However, during startup and shutdown conditions, V<sub>L</sub> can be greater than (V<sub>CC</sub> 0.4) V.
  8. Typical values are for V<sub>CC</sub> = +2.8 V, V<sub>L</sub> = +1.8 V and T<sub>A</sub> = +25°C. All units are production tested at T<sub>A</sub> = +25°C. Limits over the operating temperature range are guaranteed by design.

#### **TIMING CHARACTERISTICS**

					-4	0°C to +85°	°C	
Symbol	Parameter	Test Conditions (Note 9)	V <sub>CC</sub> (V) (Note 10)	<b>V<sub>L</sub> (V)</b> (Note 11)	Min	Typ (Note 12)	Max	Unit
t <sub>R-VCC</sub>	I/O V <sub>CC</sub> Rise Time (Output = I/O_V <sub>CC</sub> )	C <sub>IOVCC</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		0.7	2.4	ns
t <sub>F-VCC</sub>	I/O V <sub>CC</sub> Falltime (Output = I/O_V <sub>CC</sub> )	C <sub>IOVCC</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		0.5	1.0	ns
t <sub>R-VL</sub>	I/O V <sub>L</sub> Risetime (Output = I/O_V <sub>L</sub> )	C <sub>IOVL</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		1.0	3.8	ns
t <sub>F-VL</sub>	I/O V <sub>L</sub> Falltime (Output = I/O_V <sub>L</sub> )	C <sub>IOVL</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		0.6	1.2	ns
Z <sub>O-VCC</sub>	I/O V <sub>CC</sub> One-Shot Output Impedance		1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		30		Ω
Z <sub>O-VL</sub>	I/O V <sub>L</sub> One-Shot Output Impedance		1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		30	Mr.	Ω
t <sub>PD_VL-VCC</sub>	Propagation Delay (Output = I/O_V <sub>CC</sub> , t <sub>PHL</sub> , t <sub>PLH</sub> )	C <sub>IOVCC</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		4.5	12	ns
t <sub>PD_VCC-VL</sub>	Propagation Delay (Output = I/O_V <sub>L</sub> , t <sub>PHL</sub> , t <sub>PLH</sub> )	C <sub>IOVL</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	EA	3.0	7.2	ns
t <sub>SK VL-VCC</sub>	Channel-to-Channel Skew (Output = I/O_V <sub>CC</sub> )	C <sub>IOVCC</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	7/10	0.2	0.3	nS
t <sub>SK_VCC-VL</sub>	Channel-to-Channel Skew (Output = I/O_V <sub>L</sub> )	C <sub>IOVCC</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		0.2	0.3	nS
MDR	Maximum Data Rate	(Output = I/O_V <sub>CC</sub> , C <sub>IOVCC</sub> = 15 pF) (Output = I/O_V <sub>L</sub> ,	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	110 140			Mb/s
		$C_{IOVL} = (15 pF)$	> 2,2	> 1.8	140			

 <sup>9.</sup> Normal test conditions are V<sub>EN</sub> = 0 V, C<sub>IOVCC</sub> = 15 pF and C<sub>IOVL</sub> = 15 pF, unless otherwise specified.
 10. V<sub>CC</sub> is the supply voltage associated with the high voltage port, and V<sub>CC</sub> ranges from +1.3 V to 4.5 V under normal operating conditions.
 11. V<sub>L</sub> is the supply voltage associated with the low voltage port, V<sub>L</sub> must be less than or equal to (V<sub>CC</sub> – 0.4) V during normal operation. However, during startup and shutdown conditions, V<sub>L</sub> can be greater than (V<sub>CC</sub> – 0.4) V.
 12. Typical values are for V<sub>CC</sub> = +2.8 V, V<sub>L</sub> = +1.8 V and T<sub>A</sub> = +25°C. All units are production tested at T<sub>A</sub> = +25°C. Limits over the operating temperature range are guaranteed by design.

THIS DE

#### **ENABLE / DISABLE TIME MEASUREMENTS**

					-4	0°C to +85°	°C	
Symbol	Parameter	Test Conditions (Note 13)	V <sub>CC</sub> (V) (Note 14)	<b>V<sub>L</sub> (V)</b> (Note 15)	Min	Typ (Note 16)	Max	Unit
t <sub>EN-VCC</sub>	Turn-On Enable Time (Output = I/O_V <sub>CC</sub> , t <sub>pZH</sub> )	C <sub>IOVCC</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		150	200	ns
	Turn-On Enable Time (Output = I/O_V <sub>CC</sub> , t <sub>pZL</sub> )	C <sub>IOVL</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		130	180	ns
t <sub>EN-VL</sub>	Turn-On Enable Time (Output = I/O_V <sub>L</sub> , t <sub>pZH</sub> )	C <sub>IOVCC</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		95	225	ns
	Turn-On Enable Time (Output = I/O_V <sub>L</sub> , t <sub>pZL</sub> )	C <sub>IOVL</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		75	100	ns
t <sub>DIS-VCC</sub>		C <sub>IOVCC</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		175	250	ns
	Propagation Delay (Output = I/O_V <sub>CC</sub> , t <sub>PLZ</sub> )	C <sub>IOVL</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		140	160	ns
t <sub>DIS-VL</sub>	Turn-Off Disable Time (Output = $I/O_V_L$ , $t_{pHZ}$ )	C <sub>IOVCC</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)		180	275	ns
	Propagation Delay (Output = I/O_V <sub>L</sub> , t <sub>PLZ</sub> )	C <sub>IOVL</sub> = 15 pF	1.3 to 4.5	0.9 to (V <sub>CC</sub> – 0.4)	EN	160	220	ns

- 13. Normal test conditions are V<sub>EN</sub> = 0 V, C<sub>IOVCC</sub> = 15 pF and C<sub>IOVL</sub> = 15 pF, unless otherwise specified.

  14. V<sub>CC</sub> is the supply voltage associated with the high voltage port, and V<sub>CC</sub> ranges from +1.3 V to 4.5 V under normal operating conditions.

  15. V<sub>L</sub> is the supply voltage associated with the low voltage port. V<sub>L</sub> must be less than or equal to (V<sub>CC</sub> 0.4) V during normal operation. However, during startup and shutdown conditions, V<sub>L</sub> can be greater than (V<sub>CC</sub> 0.4) V.
- 16. Typical values are for  $V_{CC}$  = +2.8 V,  $V_L$  = +1.8 V and  $T_A$  = +25 °C. All units are production tested at  $T_A$  = +25 °C. Limits over the operating temperature range are guaranteed by design.

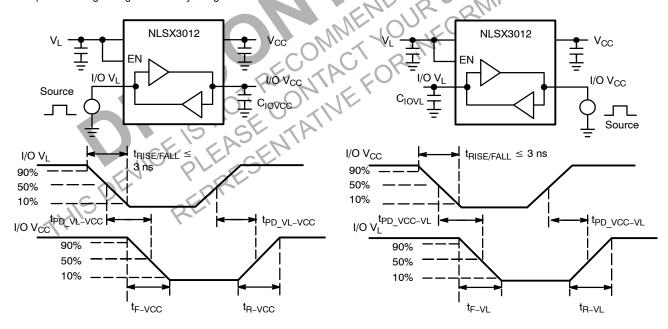
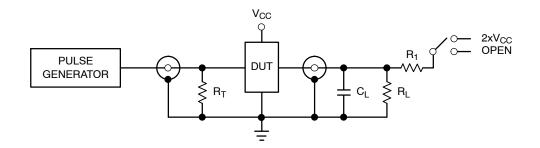


Figure 3. Driving I/O V<sub>L</sub> Test Circuit and Timing

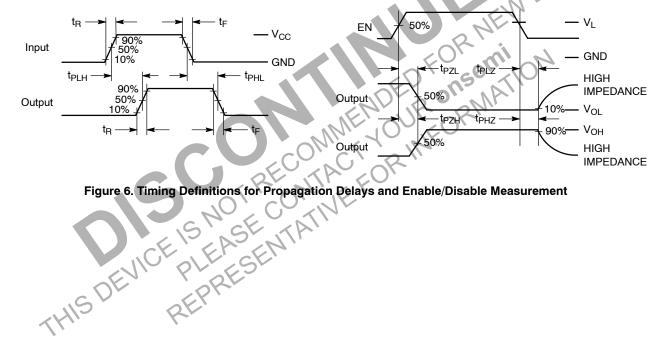
Figure 4. Driving I/O  $V_{CC}$  Test Circuit and Timing



Test	Switch
t <sub>PZH</sub> , t <sub>PHZ</sub>	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	2 x V <sub>CC</sub>

 $C_L=15$  pF or equivalent (Includes jig and probe capacitance)  $R_L=R_1=50~k\Omega$  or equivalent  $R_T=Z_{OUT}$  of pulse generator (typically 50  $\Omega)$ 

Figure 5. Test Circuit for Enable/Disable Time Measurement



#### IMPORTANT APPLICATIONS INFORMATION

#### **Level Translator Architecture**

The NLSX3012 auto sense translator provides bi–directional voltage level shifting to transfer data in multiple supply voltage systems. This device has two supply voltages,  $V_L$  and  $V_{CC}$ , which set the logic levels on the input and output sides of the translator. When used to transfer data from the  $V_L$  to the  $V_{CC}$  ports, input signals referenced to the  $V_L$  supply are translated to output signals with a logic level matched to  $V_{CC}$ . In a similar manner, the  $V_{CC}$  to  $V_L$  translation shifts input signals with a logic level compatible to  $V_{CC}$  to an output signal matched to  $V_L$ .

The NLSX3012 consists of four bi-directional channels that independently determine the direction of the data flow without requiring a directional pin. The one-shot circuits are used to detect the rising or falling input signals. In addition, the one shots decrease the rise and fall time of the output signal for high-to-low and low-to-high transitions.

#### Input Driver Requirements

Auto sense translators such as the NLSX3012 have a wide bandwidth, but a relatively small DC output current rating. The high bandwidth of the bi-directional I/O circuit is used to quickly transform from an input to an output driver and vice versa. The I/O ports have a modest DC current output specification so that the output driver can be over driven when data is sent to in the opposite direction.

For proper operation, the input driver to the auto sense translator should be capable of driving 2 mA of peak output current with an output impedance less than 25  $\Omega$ . The bi-directional configuration of the translator results in both input stages being active for a very short time period. Although the peak current from the input signal circuit is relatively large, the average current is small and consistent with a standard CMOS input stage.

#### **Output Load Requirements**

The NLSX3012 is designed to drive CMOS inputs. Resistive pullup or pulldown loads of less than 50 k $\Omega$  should not be used with this device. The NLSX3373 or NLSX3378 open–drain auto sense translators are alternate

translator options for an application such as the I<sup>2</sup>C bus that requires pullup resistors.

#### **Enable Input (EN)**

The NLSX3012 has an Enable pin (EN) that provides tri–state operation at the I/O pins. Driving the Enable pin to a low logic level minimizes the power consumption of the device and drives the I/O  $V_{\rm CC}$  and I/O  $V_{\rm L}$  pins to a high impedance state. Normal translation operation occurs when the EN pin is equal to a logic high signal. The EN pin is referenced to the  $V_{\rm L}$  supply and has Over–Voltage Tolerant (OVT) protection.

#### Uni-Directional versus Bi-Directional Translation

The NLSX3012 can function as a non-inverting uni-directional translator. One advantage of using the translator as a uni-directional device is that each I/O pin can be configured as either an input or output. The configurable input or output feature is especially useful in applications such as SPI that use multiple uni-directional I/O lines to send data to and from a device. The flexible I/O port of the auto sense translator simplifies the trace connections on the PCB.

# **Power Supply Guidelines**

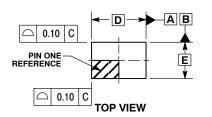
It is recommended that the  $V_L$  supply should be less than or equal to the value of the  $V_{CC}$  minus 0.4 V. The sequencing of the power supplies will not damage the device during the power up operation; however, the current consumption of the device will increase if  $V_L$  exceeds  $V_{CC}$  minus 0.4 V. In addition, the I/O  $V_{CC}$  and I/O  $V_L$  pins are in the high impedance state if either supply voltage is equal to 0 V.

For optimal performance, 0.01 to 0.1  $\mu F$  decoupling capacitors should be used on the  $V_L$  and  $V_{CC}$  power supply pins. Ceramic capacitors are a good design choice to filter and bypass any noise signals on the power supply voltage lines to the ground plane of the PCB. The noise immunity will be maximized by placing the capacitors as close as possible to the supply and ground pins, along with minimizing the PCB connection traces.

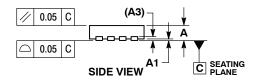
SCALE 4:1

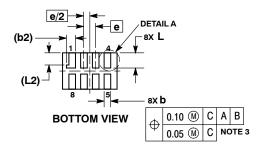


**DATE 08 NOV 2006** 

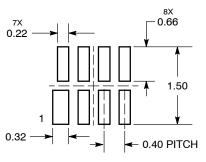








#### **MOUNTING FOOTPRINT SOLDERMASK DEFINED**



DIMENSIONS: MILLIMETERS

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  DIMENSION & APPLIES TO PLATED
- DINICIPION D APPLIES TO PLATED
  TERMINAL AND IS MEASURED BETWEEN
  0.15 AND 0.30 mm FROM TERMINAL TIP.
  MOLD FLASH ALLOWED ON TERMINALS
  ALONG EDGE OF PACKAGE, FLASH MAY
  NOT EXCEED 0.03 ONTO BOTTOM
  SURFACE OF TERMINALS.
  DETAIL A SHOWS ODTIONAL
- DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A3	0.127	REF		
b	0.15 0.25			
b2	0.30	REF		
D	1.80	BSC		
E	1.20	BSC		
е	0.40	BSC		
L	0.45	0.55		
L1	0.00 0.03			
L2	0.40	REF		

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON23417D	Electronic versions are uncontrolled except when accessed directly from the Document Repo Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	UDFN8 1.8X1.2, 0.4P		PAGE 1 OF 1	

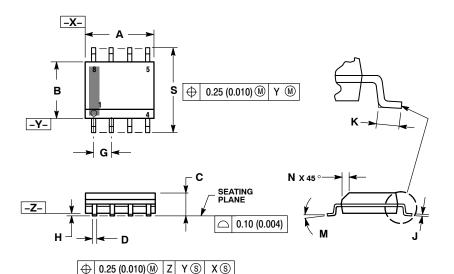
ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.





#### SOIC-8 NB CASE 751-07 **ISSUE AK**

**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

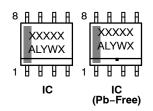
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

# **SOLDERING FOOTPRINT\***



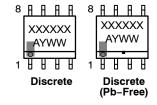
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week W

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42564B	B42564B Electronic versions are uncontrolled except when accessed directly from the Document Reportant Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

### SOIC-8 NB CASE 751-07 ISSUE AK

### **DATE 16 FEB 2011**

			DITTE TO LED 2
STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	8. DRAIN 1  STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16:  PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE STYLE 22: PIN 1. I/O LINE 1	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 STYLE 23: PIN 1. LINE 1 IN	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN STYLE 24: PIN 1. BASE
2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30:     PIN 1. DRAIN 1     2. DRAIN 1     3. GATE 2     4. SOURCE 2     5. SOURCE 1/DRAIN 2     6. SOURCE 1/DRAIN 2     7. SOURCE 1/DRAIN 2     8. GATE 1		

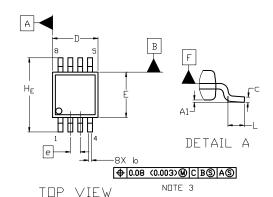
DOCUMENT NUMBER:	98ASB42564B	Printed versions are uncontrolled except when stamped "CONTROLLED	COPY" in red.
DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2

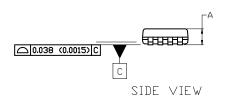
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.



#### Micro8 CASE 846A-02 ISSUE K

**DATE 16 JUL 2020** 

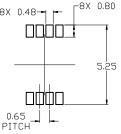






#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DDES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



RECOMMENDED MOUNTING FOOTPRINT

MID	MI	LLIMETE	RS		
DIM	MIN.	N□M.	MAX.		
Α	-	-	1.10		
A1	0.05	0.08	0.15		
b	0.25	0.33	0.40		
С	0.13	0.18	0.23		
D	2.90	3.00	3.10		
E	2.90	3.00	3.10		
e	0.65 BSC				
HE	4.75	4.90	5.05		
L	0.40	0.55	0.70		

#### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code Α = Assembly Location

Υ = Year W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. SOURCE	PIN 1. SOURCE 1	PIN 1. N-SOURCE
<ol><li>SOURCE</li></ol>	2. GATE 1	2. N-GATE
<ol><li>SOURCE</li></ol>	3. SOURCE 2	<ol><li>P-SOURCE</li></ol>
<ol><li>GATE</li></ol>	4. GATE 2	4. P-GATE
<ol><li>DRAIN</li></ol>	5. DRAIN 2	5. P-DRAIN
<ol><li>DRAIN</li></ol>	6. DRAIN 2	6. P-DRAIN
7. DRAIN	7. DRAIN 1	7. N-DRAIN
8. DRAIN	8. DRAIN 1	8. N-DRAIN

DOCUMENT NUMBER:	98ASB14087C	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	MICRO8		PAGE 1 OF 1	

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales